

NextPower 100 V, 18 mΩ N-channel MOSFET in I2PAK package

10 April 2017

Product data sheet

1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

2. Features and benefits

- · Optimised for fast switching, low spiking, high efficiency
- Low Q_G x R_{DSon} FOM for high efficiency switching applications
- Low body diode losses (Q_{rr}) and fast recovery (t_{rr})
- Strong avalanche energy rating (E_{AS})
- Avalanche rated & 100% tested
- Ha-free & RoHS compliant I2PAK low-height package

3. Applications

- Synchronous rectification in AC-to-DC and DC-to-DC applications
- Brushed & BLDC motor control
- UPS & solar inverter
- LED lighting
- Battery protection
- Full-bridge & half-bridge applications
- Flyback & resonant topologies

4. Quick reference data

| Table 1. Qui | ck reference data | | | | | | |
|---------------------|----------------------------------|------------------------------------------------------------------------------------|-----|-----|------|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | - | 100 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | - | 53 | А |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | - | 111 | W |
| Tj | junction temperature | | | -55 | - | 175 | °C |
| Static chara | acteristics | | | | | _ | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 10 | | - | 15 | 18 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 11 | | - | 22 | 28 | mΩ |
| Dynamic ch | naracteristics | ' | | | | | |
| Q _{GD} | gate-drain charge | I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; | | - | 4.2 | - | nC |
| Q _{G(tot)} | total gate charge | Fig. 12; Fig. 13 | | - | 21.4 | - | nC |

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| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|----------------------|-----------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| Avalanche ruggedness | | | | | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $\begin{array}{l} {\sf I}_{\sf D} = 20.5 \; {\sf A}; \; {\sf V}_{sup} \le \; 100 \; {\sf V}; \; {\sf R}_{\sf GS} = 50 \; \Omega; \\ {\sf V}_{\sf GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; ^{\circ}{\rm C}; \; \underline{{\sf Fig. 4}}; \\ {\sf Unclamped} \end{array}$ | [2] | - | - | 109 | mJ |

[1] Avalanche current is limited by I_{AS}

[2] Protected by 100% test

5. Pinning information

| Table 2. Pinning information | | | | | |
|------------------------------|--------|-----------------------------------|--------------------|----------------|--|
| Pin | Symbol | Description | Simplified outline | Graphic symbol | |
| 1 | G | gate | mb | D | |
| 2 | D | drain | | | |
| 3 | S | source | | G-UFFA | |
| mb | D | mounting base; connected to drain | | mbb076 S | |
| | | | I2PAK (SOT226) | | |

6. Ordering information

| Table 3. Ordering information | | | | | | |
|-------------------------------|---------|------------------------------------------------------------------------------------------------|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| PSMN018-100ESF | I2PAK | plastic, single-ended package (I2PAK); 3 terminals; 2.54 mm pitch; 11 mm x 10 mm x 4.3 mm body | SOT226 | | | |

7. Marking

| Table 4. Marking codes | |
|------------------------|----------------|
| Type number | Marking code |
| PSMN018-100PSF | PSMN018-100PSF |

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8. Limiting values

Table 5. Limiting values

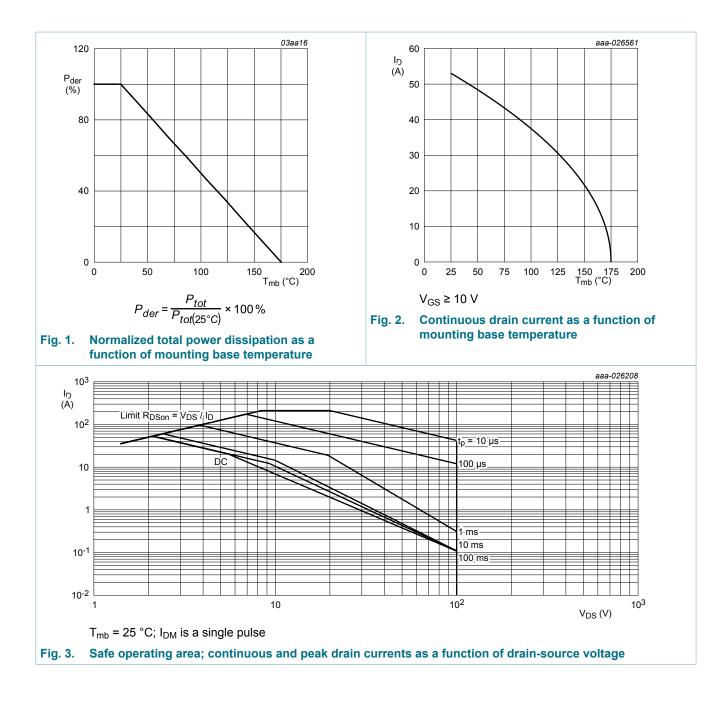
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|-----------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | | - | 100 | V |
| V _{DGR} | drain-gate voltage | 25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ | | - | 100 | V |
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | | - | 111 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | [1] | - | 53 | А |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | | - | 37 | А |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3 | | - | 212 | А |
| T _{stg} | storage temperature | | | -55 | 175 | °C |
| Tj | junction temperature | | | -55 | 175 | °C |
| T _{sld(M)} | peak soldering temperature | | | - | 260 | °C |
| Source-drain | n diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 53 | А |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 212 | А |
| Avalanche r | uggedness | | _ | | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $ \begin{array}{l} I_{D} = 20.5 \; \text{A}; \; V_{sup} \leq \; 100 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \overline{\text{Fig. 4}}; \\ \text{Unclamped} \end{array} $ | [2] | - | 109 | mJ |
| I _{AS} | non-repetitive avalanche current | | [2] | - | 20.5 | A |

[1] Avalanche current is limited by I_{AS}

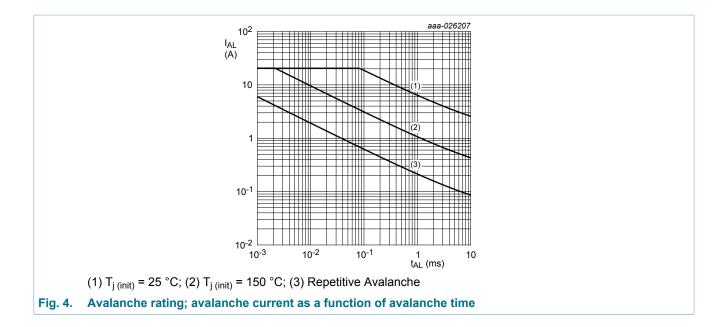
[2] Protected by 100% test

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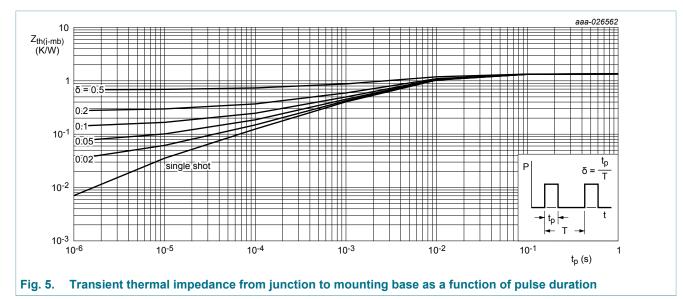
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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------------------------|---------------|-----|------|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | <u>Fig. 5</u> | - | 1.22 | 1.35 | K/W |



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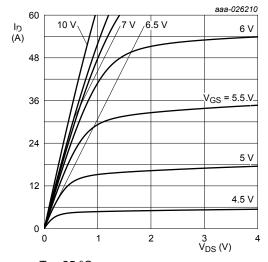
10. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------------|----------------------------------------------------------|-------------------------------------------------------------------------------------------------|-----|------|-----|------|
| Static charac | cteristics | | | | | |
| V _{(BR)DSS} | drain-source | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 100 | - | - | V |
| . , | breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C | 90 | - | - | V |
| V _{GS(th)} | gate-source threshold | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C | - | 3.6 | - | V |
| | voltage | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C | - | 2.1 | - | V |
| | | I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9</u> | 2 | 3.2 | 4 | V |
| $\Delta V_{GS(th)} / \Delta T$ | gate-source threshold voltage variation with temperature | 25 °C ≤ T _j ≤ 175 °C | - | -7.1 | - | mV/K |
| I _{DSS} | drain leakage current | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.01 | 1 | μA |
| | | V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C | - | - | 100 | μA |
| I _{GSS} | gate leakage current | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 5 | 100 | nA |
| | | V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C | - | 5 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 10</u> | - | 15 | 18 | mΩ |
| | | V _{GS} = 7 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 10</u> | - | 17.9 | 27 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; <u>Fig. 11</u> | - | 22 | 28 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; <u>Fig. 11</u> | - | 31 | 40 | mΩ |
| R _G | gate resistance | f = 1 MHz | - | 1.58 | - | Ω |
| Dynamic cha | aracteristics | | · | | | |
| Q _{G(tot)} | total gate charge | I _D = 15 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 12; Fig. 13 | - | 21.4 | - | nC |
| | | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$ | - | 10.9 | - | nC |
| Q _{GS} | gate-source charge | I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; | - | 7.2 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | Fig. 12; Fig. 13 | - | 4.3 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate- source charge | | - | 2.9 | - | nC |
| Q _{GD} | gate-drain charge | | - | 4.2 | - | nC |
| V _{GS(pl)} | gate-source plateau voltage | I _D = 15 A; V _{DS} = 50 V; <u>Fig. 12; Fig. 13</u> | - | 4.9 | - | V |
| C _{iss} | input capacitance | V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; | - | 1482 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C; <u>Fig. 14</u> | - | 280 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 13 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 50 \text{ V}; \text{ R}_{L} = 3.3 \Omega; \text{ V}_{GS} = 10 \text{ V};$ | - | 10.2 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega; T_j = 25 °C$ | - | 14.1 | - | ns |

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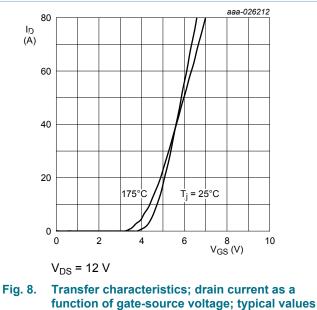
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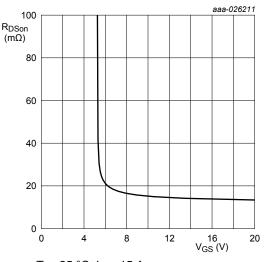
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|-----------------------|-------------------------------------------------------------------------|--|-----|------|-----|------|
| t _{d(off)} | turn-off delay time | | | - | 17.3 | - | ns |
| t _f | fall time | | | - | 12.6 | - | ns |
| Source-drain | Source-drain diode | | | | | | |
| V _{SD} | source-drain voltage | I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u> | | - | 0.9 | 1.2 | V |
| t _{rr} | reverse recovery time | I_{S} = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V; | | - | 40 | - | ns |
| Qr | recovered charge | V _{DS} = 50 V; <u>Fig. 16</u> | | - | 46 | - | nC |

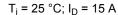














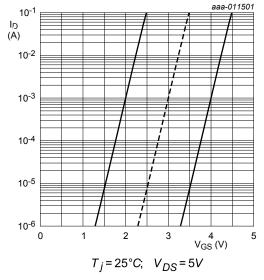
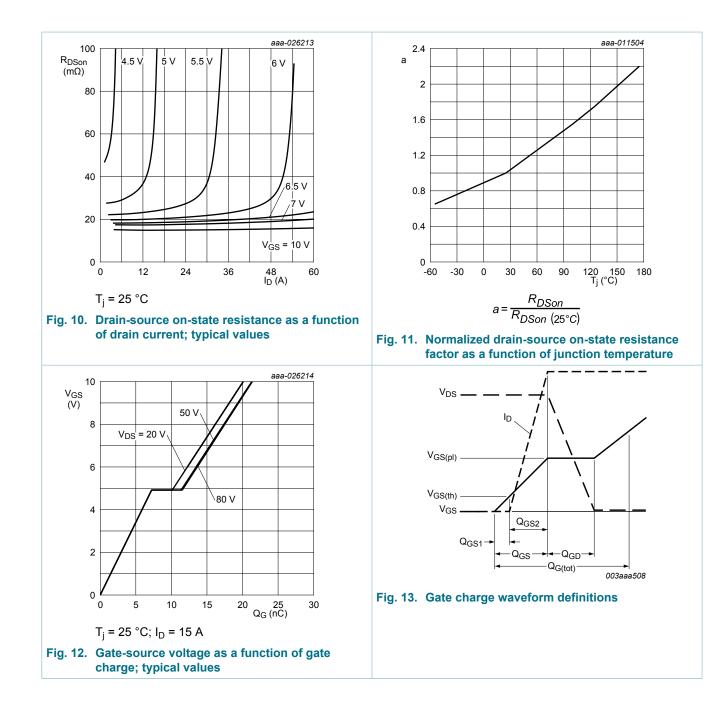


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

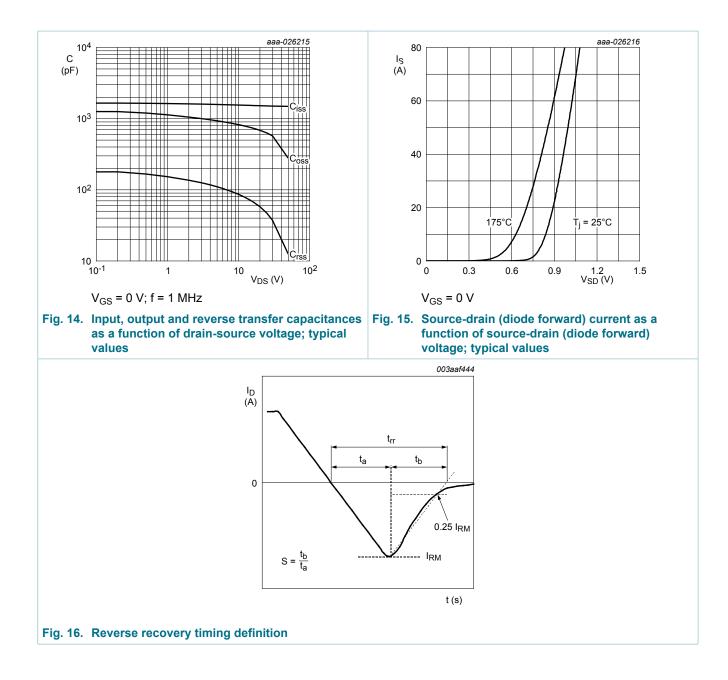
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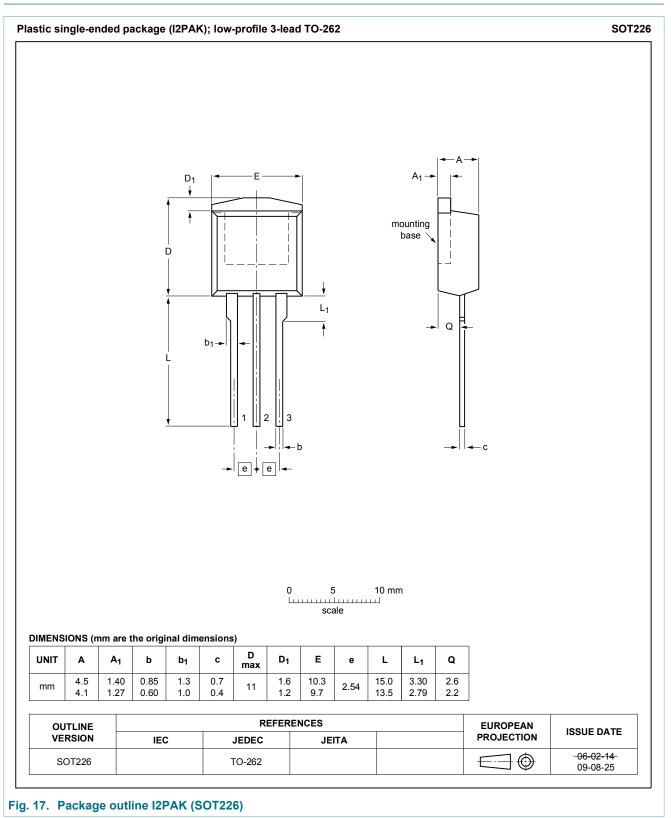


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11. Package outline



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12. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|-----------------------|---------------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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